

The temporal and spatial pinhole constraint in small molecule hole transport layers for stable and efficient perovskite photovoltaics

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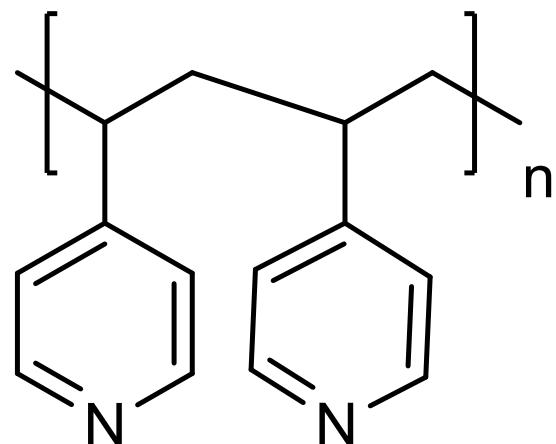


Figure S1 The chemical structure of poly(4-vinylpyridine) (P4VP).

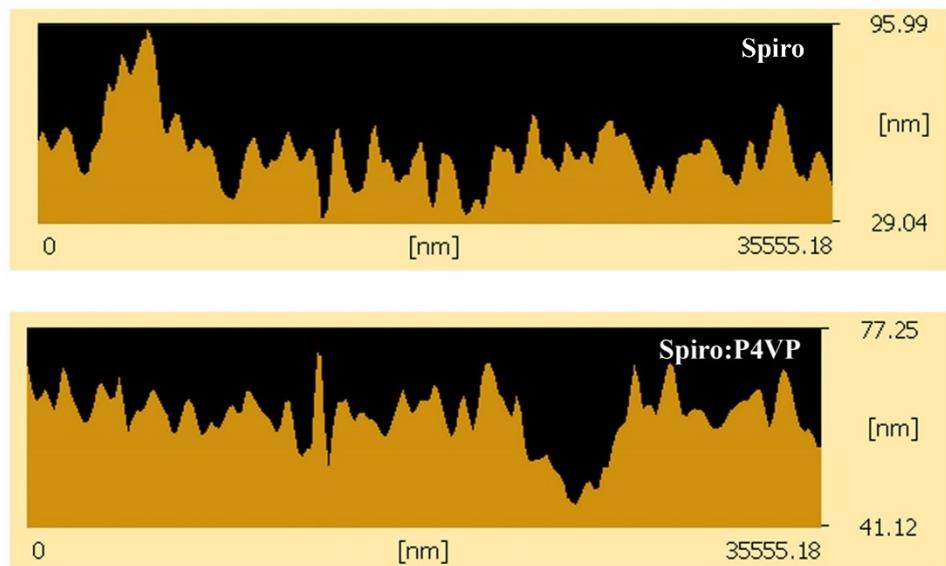


Figure S2 The RMS roughness data for Spiro and Spiro:P4VP based sample

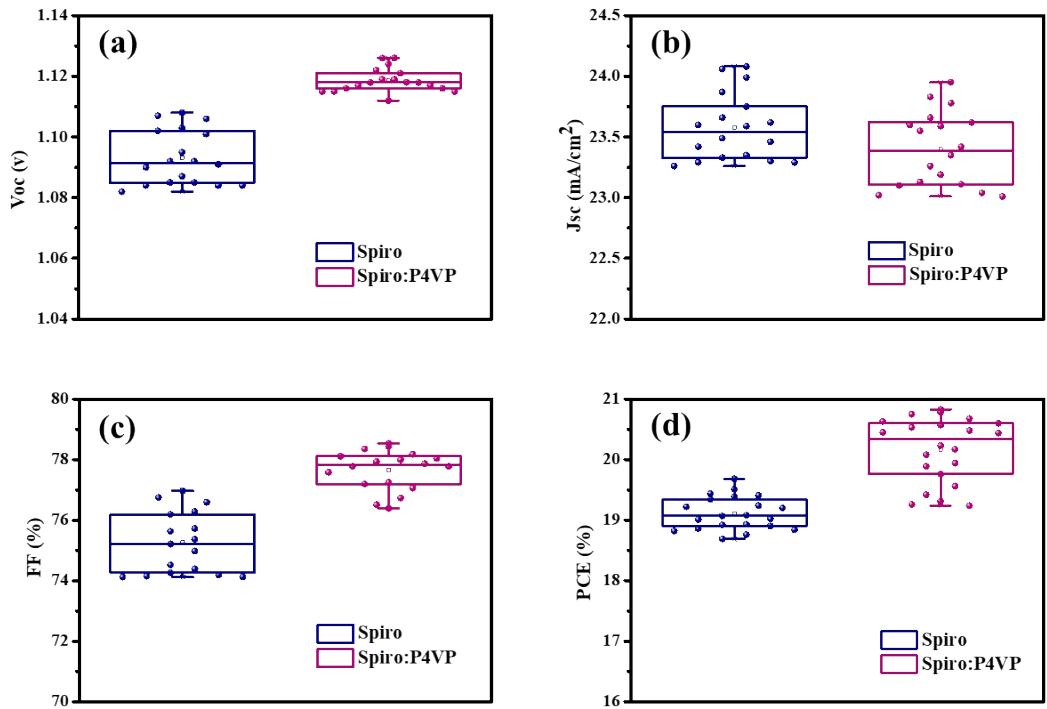
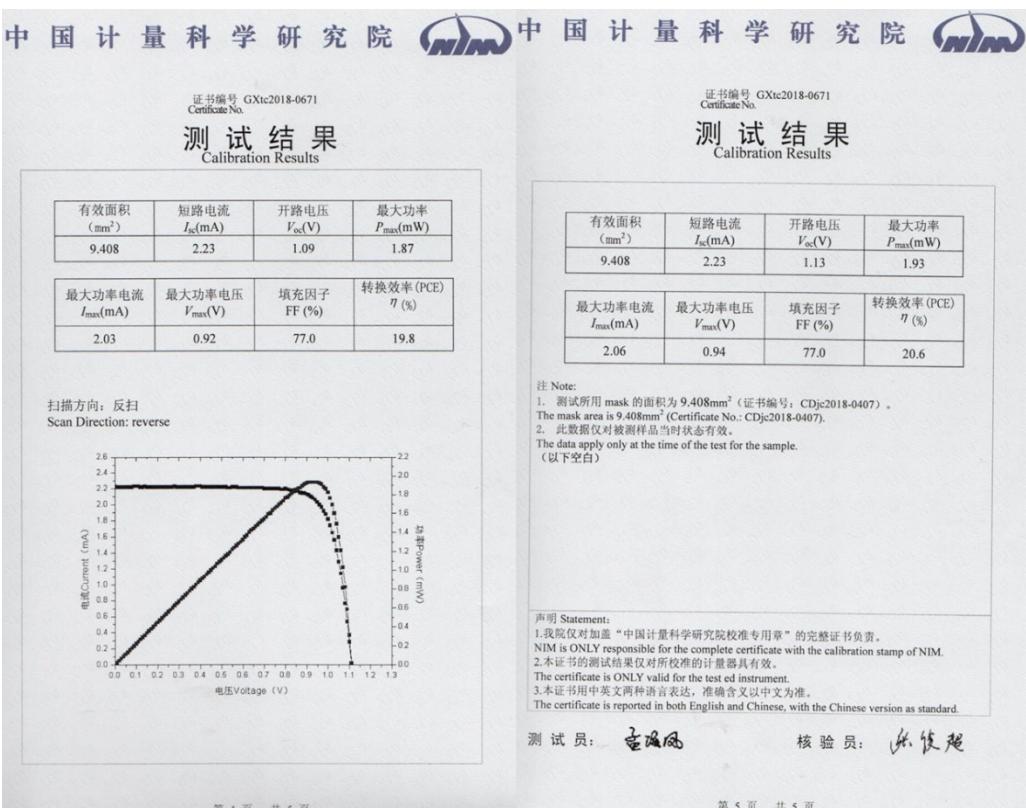


Figure S3. a) The open circuit voltage. b) The short-circuit current. c) The fill factor. d) The power conversion efficiency of multi-devices based on Spiro and Spiro:P4VP as HTLs.



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测试结果
Calibration Results

1. 测试条件 Test Conditions:

标准太阳电池: 单晶硅 (81#);
Reference Solar Cell: mono-Si (81#);
太阳模拟器: 双光源太阳模拟器, AAA 级;
Solar Simulator Classification: double-light source in AAA classification;
温度传感器/控制系统: 无;
Temperature Sensor/Control System: None;
Mask (Y/N) : Y;
电压设置: -0.1V~1.2V; 间隔: 0.01V
Scan Parameter: From -0.1V to 1.2V with 0.01V interval
光圈 Mask (Y/N) : Y
扫描时间: 39 秒 扫描点数: 131

Figure S4. Certificated results by National Institute of Metrology, China (NIM, China). The forward scan is performed from -0.1 V to 1.2 V at 33 mV/s, with a PCE of 19.8% ($V_{oc}=1.09$ V, $I_{sc}=2.23$ mA, FF=77.0%). The reverse scan is performed from 1.2 V to -0.1 V at 33 mV/s, with a PCE of 20.6% ($V_{oc}=1.13$ V, $I_{sc}=2.23$ mA, FF=77.0%). The device has an active area of 0.09408 cm 2 .

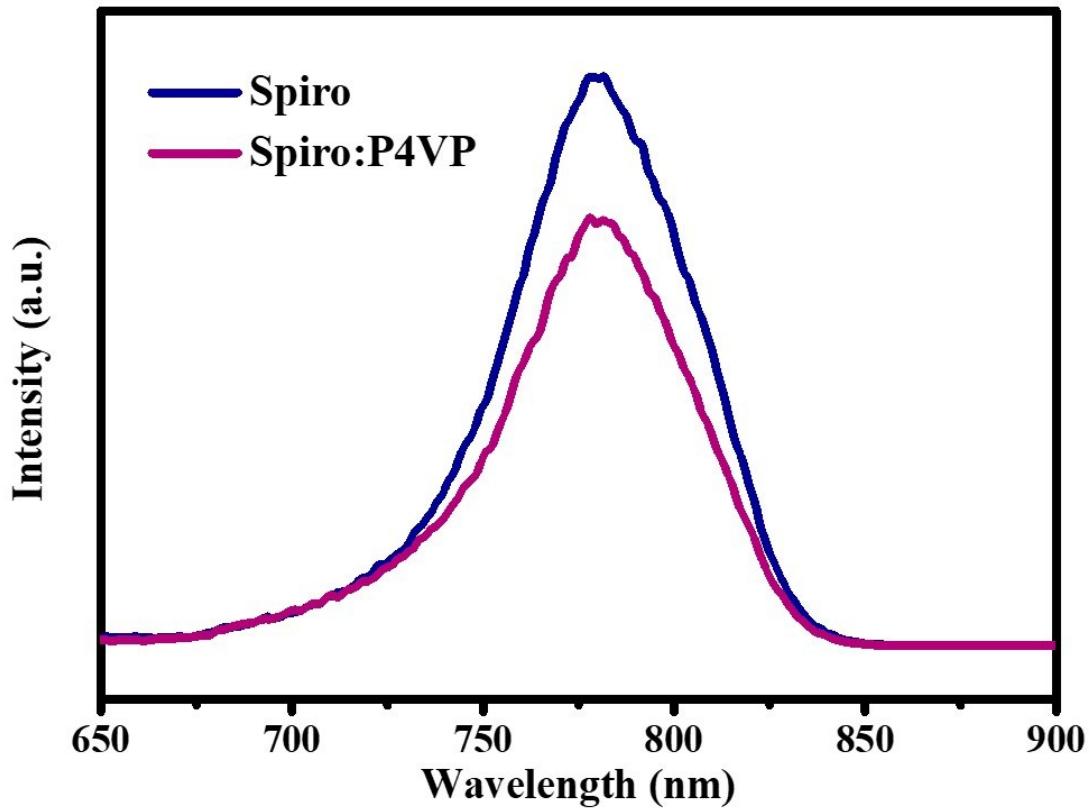


Figure S5. The steady-state photoluminescence (PL) spectroscopy based on Spiro and Spiro:P4VP as HTLs.

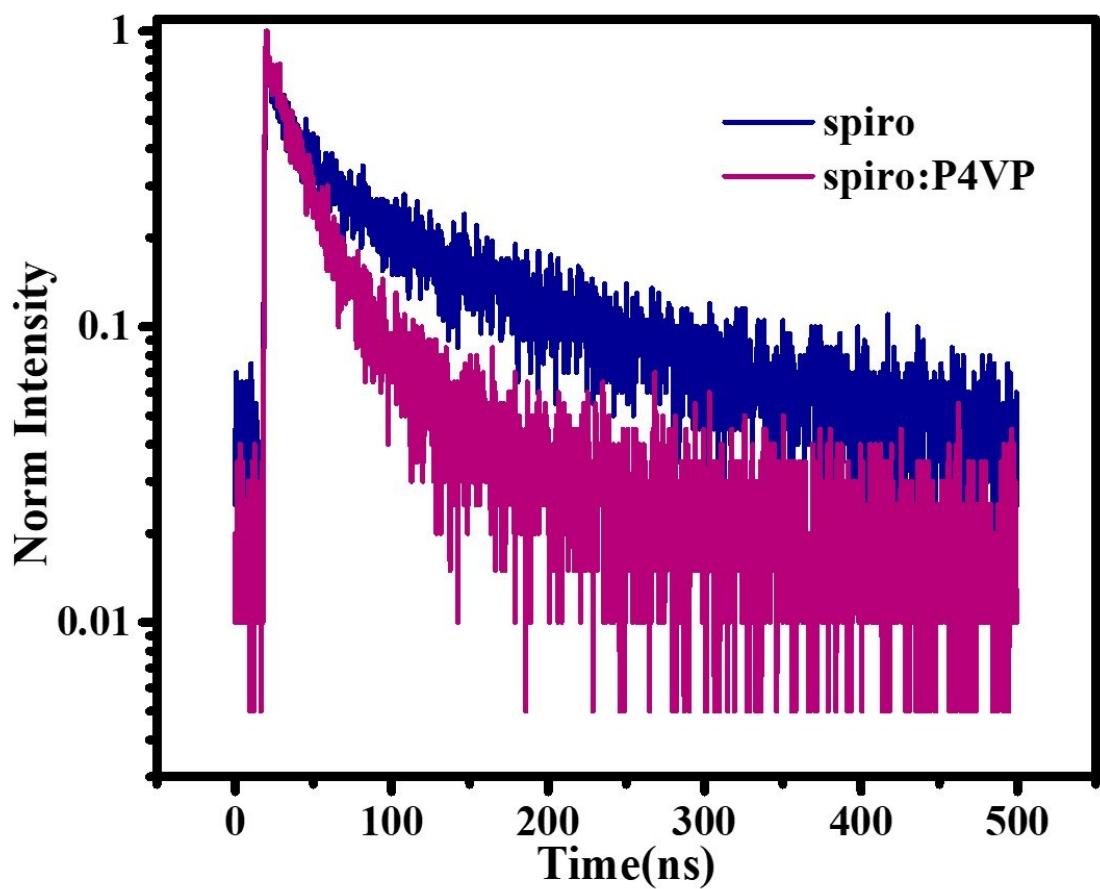


Figure S6. The normalized time-resolved photoluminescence (TRPL) spectroscopy based on Spiro and Spiro:P4VP as HTLs.

Table S1. The obtained carrier lifetimes of perovskite films based on Spiro and Spiro:P4VP as HTLs.

Sample	Spiro	Spiro:P4VP
Lifetime τ_1 /ns	12.03	23.60
Lifetime τ_2 /ns	112.1	100.0

Table S2. The obtained photovoltage decay time ($\tau_{\text{recombination}}$) and photocurrent decay time ($\tau_{\text{transport}}$) of perovskite solar cells based on Spiro and Spiro:P4VP as HTLs.

Sample	$\tau_{\text{recombination}}$	$\tau_{\text{transport}}$
Spiro	0.51μs	310ns
Spiro:P4VP	0.70μs	220ns

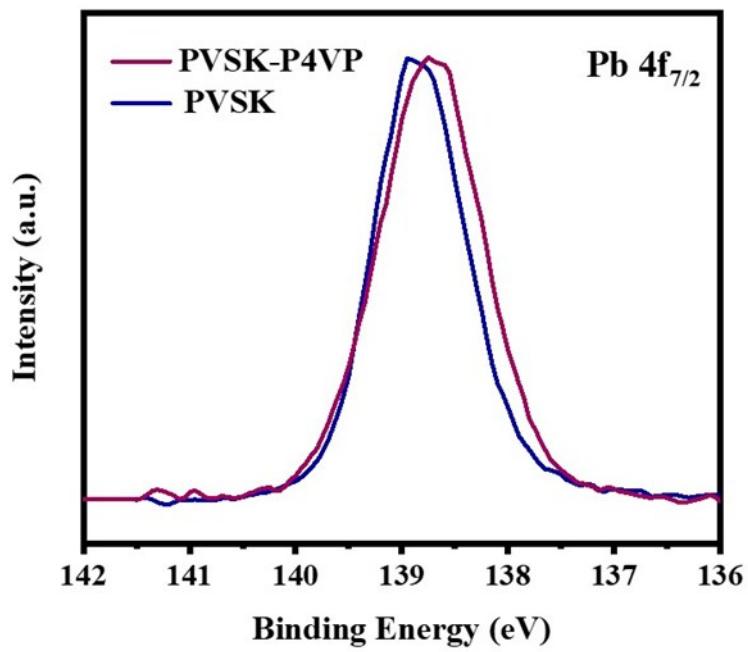


Figure S7 . XPS survey spectra of Pb atom in perovskite films without and with P4VP (0.1 mg mL^{-1})

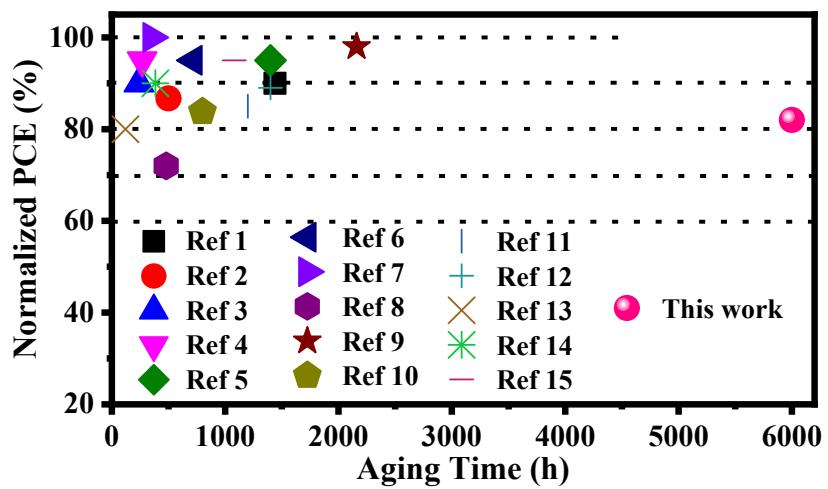


Figure S8 . The stability of this work stored in air was compared with other works.

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